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Should be replaced with:

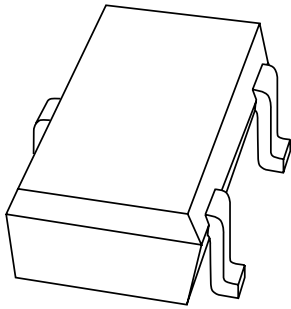
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMST6428; PMST6429 NPN general purpose transistors

Product data sheet
Supersedes data of 1997 Jun 12

1999 Apr 22

NPN general purpose transistors

PMST6428; PMST6429

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 50 V).

APPLICATIONS

- General purpose switching and amplification in e.g. telephony and professional communication equipment.

DESCRIPTION

NPN transistor in an SC-70; SOT323 plastic package.

MARKING

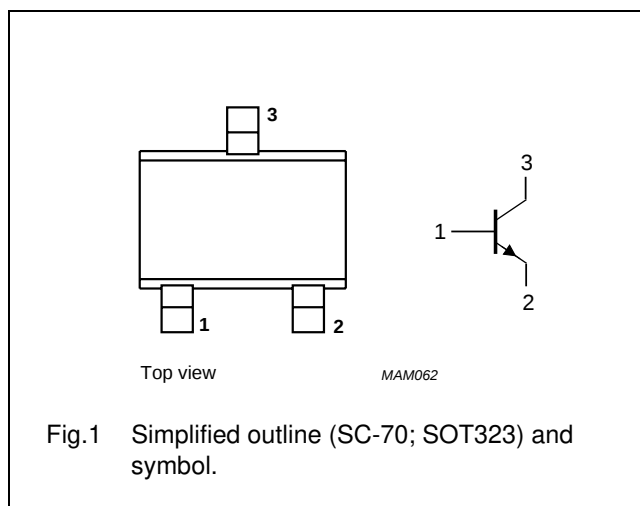
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST6428	*1K
PMST6429	*1L

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	PMST6428		—	60	V
	PMST6429		—	55	V
V_{CEO}	collector-emitter voltage	open base			
	PMST6428		—	50	V
	PMST6429		—	45	V
V_{EBO}	emitter-base voltage	open collector	—	6	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} \leq 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 30\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 30\text{ V}$; $T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain PMST6428	$V_{CE} = 5\text{ V}$ $I_C = 0.01\text{ mA}$	250	–	
		$I_C = 0.1\text{ mA}$	250	650	
		$I_C = 1\text{ mA}$	250	–	
		$I_C = 10\text{ mA}$	250	–	
	DC current gain PMST6429	$V_{CE} = 5\text{ V}$ $I_C = 0.01\text{ mA}$	500	–	
		$I_C = 0.1\text{ mA}$	500	1250	
		$I_C = 1\text{ mA}$	500	–	
		$I_C = 10\text{ mA}$	500	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}$; $I_B = 0.5\text{ mA}$; note 1	–	200	mV
		$I_C = 100\text{ mA}$; $I_B = 5\text{ mA}$; note 1	–	600	mV
V_{BE}	base-emitter voltage	$I_C = 1\text{ mA}$; $V_{CE} = 5\text{ V}$	560	660	mV
C_c	collector capacitance	$I_E = I_C = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$	–	3	pF
C_e	emitter capacitance	$I_C = I_E = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = 1\text{ mA}$; $V_{CE} = 5\text{ V}$; $f = 100\text{ MHz}$	100	700	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

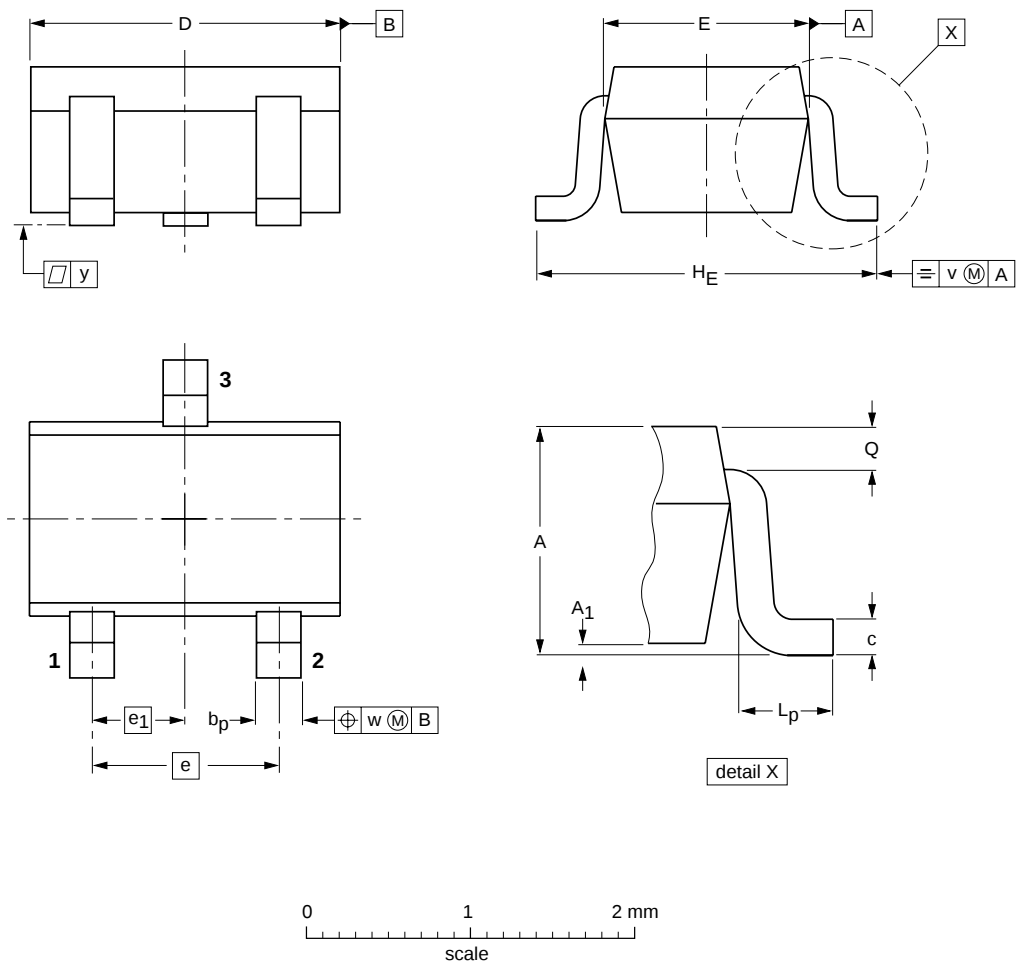
NPN general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN general purpose transistors

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: **<http://www.nxp.com>**

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